



Silicon Schottky Barrier Diode

FEATURES

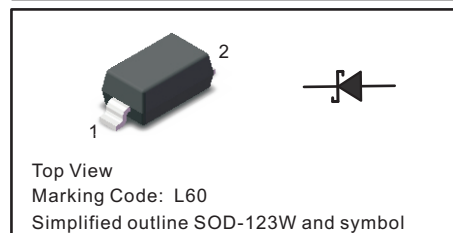
- Metal silicon junction, majority carrier conduction
- Ideal for used in detection or for switching on the radio, TV, etc.

MECHANICAL DATA

- Case: SOD-123W
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 16mg/0.00056oz

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbols	LL60PW	Units
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	20	V
Average Rectified Output Current	I_O	50	mA
Peak Forward Current	I_{FM}	150	mA
Surge Forward Current	I_{surge}	500	mA
Forward Current at $V_F < 1V$	I_F	4	mA
Reverse Current at $V_R = 10V$	I_R	50	uA
Total Capacitance at $f = 1MHz, V_R = 1V$	C_{tot}	38	pF
Rectification efficiency at $V_i = 2 V_{RMS}, R = 5 K\Omega$	η	55	%
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55 ~ +150	°C

Fig.1 Forward Characteristics

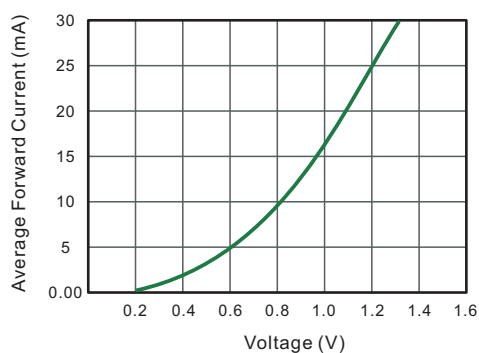
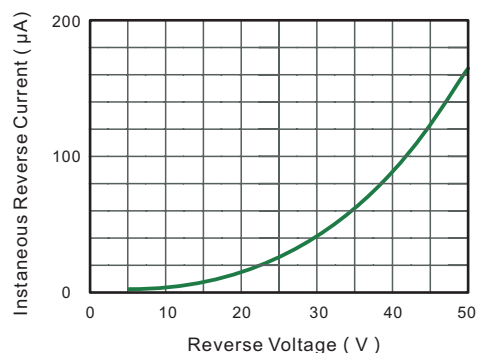


Fig.2 Typical Reverse Characteristics

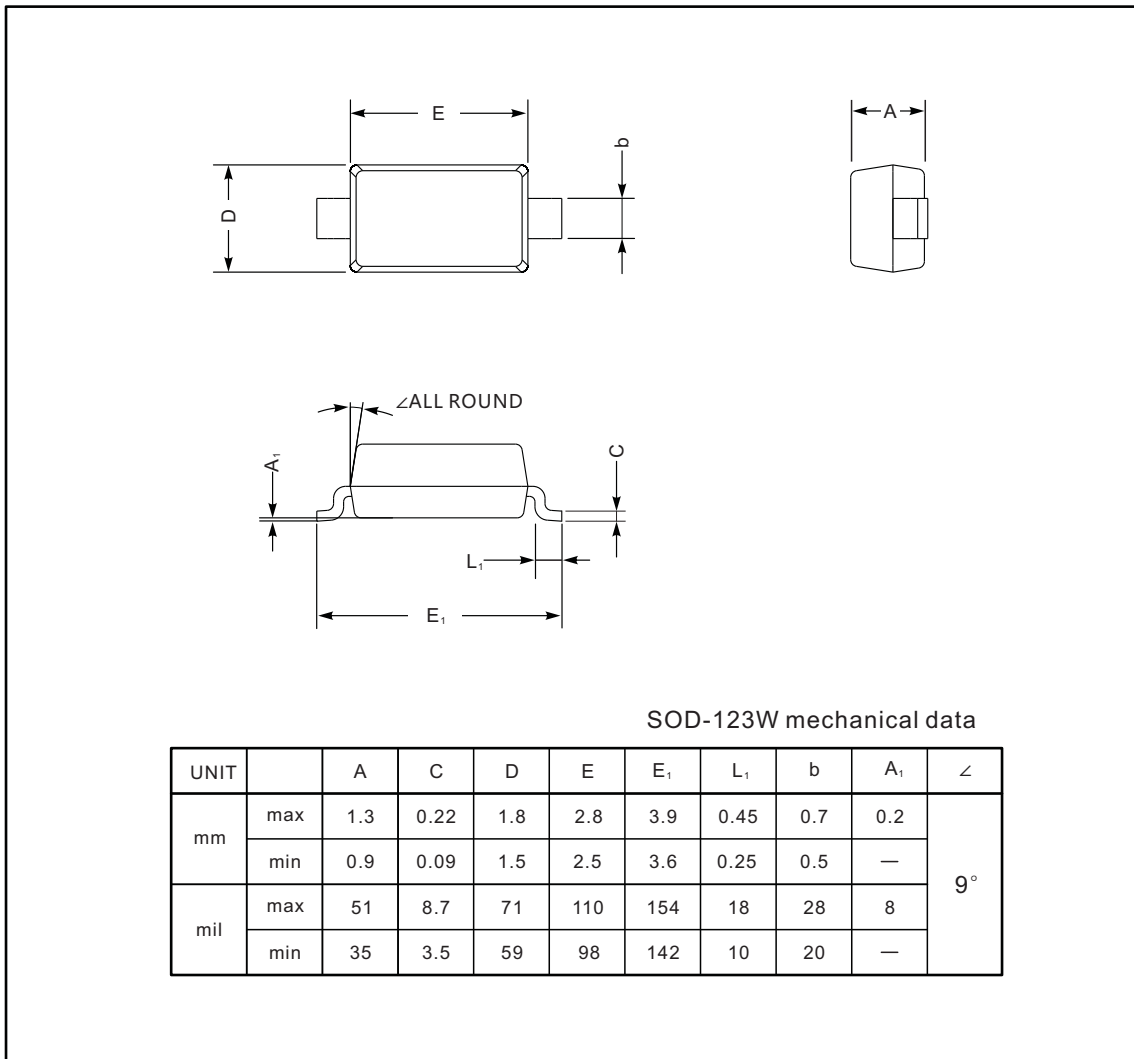




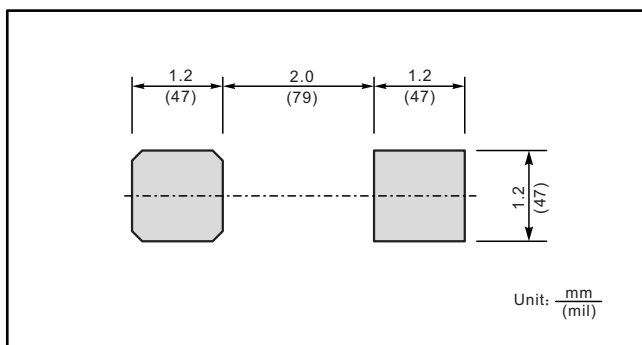
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123W



The recommended mounting pad size



Marking

Type number	Marking code
LL60PW	L60